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Molecular processes at interfaces and in thin films

- Understanding electronically and thermally induced elementary processes in molecular ensembles
- Analysis > Electronic structure
 - Structural properties
 - Dynamics of electronically excited states







Controlled modification of interface properties



Understanding binding properties

Graphene nanoribbons



Tuning of electronic properties

π -conjugated organic materials



Understanding optoelectronic properties

Molecule-substrate interactions



Two-photon photoemission (2PPE)



electronic structure, dynamics, dispersion

High-resolution electron energy loss spectroscopy (HREELS)



Second harmonic generation (SHG)



electronic properties, dynamics

Temperature programmed desorption (TPD)



Coverage & binding energies

Motivation



Optoelectronic devices





- 1. Light absorption
- 2. Exciton generation
- 3. Exciton separation
- 4. Charge transport
- 5. Charge extraction







Energy level alignment (electron/hole injection barriers)

Charge carrier and exciton dynamics at the interface and within the film

Correlation between the electronic structure as well as dynamics (lifetimes) of the excited states and the energy conversion efficiency



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tunable Ti:Sapphire laser system



- electronic structure
- occupied and unoccupied states
- time-resolved: lifetimes
- angle-resolved: dispersion





Electronic structure: 6T/Au(111)







Electronic structure



 \rightarrow Exciton binding energy: 0.9 eV

Exciton dynamics





Time-Resolved Second Harmonic Generation (TR-SHG)





Charge separation at P3HT/C₆₀ interface







Graphene Nanoribbons (GNR)



Graphene

A. H. Castro Neto et al., Rev. Mod. Phys. 81, 109 (2009)



adapted from: J. Bai et al., Nature Nanotechnology 5, 655 (2010)



K. Nakada et al., Phys. Rev. B 54, 17954 (1996)



Top-down GNR fabrication techniques

• Lithographic patterning

(etch mask formed in electron beam)

• Exfoliating graphene

(annealing graphite in hydrogen gas)

• Unzipping carbon nanotubes

(using KMnO₄)

• Problem:

- Edges' quality is unclear
- Relatively wide GNRs
- Defects (Chemical preparation)



M. Y. Han *et al.*, Phys. Rev. Lett. **98**, 206805 (2007)
X. Li *et al.*, Science **319**, 1229 (2008)
D. V. Kosynkin *et al.*, Nature **458**, 872 (2009)



Au(111) surface J. Cai et al., Nature 466, 470 (2010) Precursor T_s=470 K: C-C coupling 1 nm 3.8 Å Polymer T_s=670 K: Cyclodehydrogenation

Graphene nanoribbon





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Br









High-resolution electron energy loss spectroscopy (HREELS)



- Vibrational spectroscopy: molecular orientation
- Electronic transitions:
 optical gap, optically forbidden transitions

Two scattering regimes

- Specular geometry Φ_i=Φ_r
- Off-specular geometry Φ_i≠Φ_r

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Following GNR formation with HREELS



Pronounced changes

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Higher elastic peak

Increased dipoleactivity of bending



- VB shifts to lower energies
- Band gap of 2.8eV independent of doping

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- Shift of approx. 0.1 eV/N to lower energies
- o Band gap size remains unaffected
- Atomcially **precise** dopant concentration and position
- Does not interfere with bottom-up synthesis







Bachelor-, Master- & PhD – positions available!!

